

## ON SOME ASPECTS OF THE CRYSTAL GROWTH

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The growth of artificial crystals of polygonal cross-section is considered in case of constant temperature and pressure. The growth process is described by the 3D reaction-diffusion equation with the appropriate initial-boundary conditions [1,2,3]. By the separation of variables the problem is reduced to 2D problem. We use a conformal mapping method and obtained the effective solutions of the problem.

### References

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